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## **VS-ST330CL Series**

Vishay Semiconductors



## Phase Control Thyristors (Hockey PUK Version), 650 A



TO-200AC (B-PUK)

PRODUCT SUM	PRODUCT SUMMARY							
Package	TO-200AC (B-PUK)							
Diode variation	Single SCR							
I <sub>T(AV)</sub>	650 A							
V <sub>DRM</sub> /V <sub>RRM</sub>	400 V, 800 V, 1200 V, 1400 V, 1600 V							
V <sub>TM</sub>	1.90 V							
I <sub>GT</sub>	100 mA							
TJ	-40 °C to 125 °C							

#### FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case TO-200AC (B-PUK)
- High profile hockey PUK
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
1		650	A				
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C				
<b>I</b>		1230	A				
I <sub>T</sub> (RMS)	T <sub>hs</sub>	25	°C				
1	50 Hz	9000	٨				
ITSM	60 Hz	9420	A				
l <sup>2</sup> t	50 Hz	405	- kA <sup>2</sup> s				
1-1	60 Hz	370	KA-S				
V <sub>DRM</sub> /V <sub>RRM</sub>		400 to 1600	V				
t <sub>q</sub>	Typical	100	μs				
TJ		-40 to +125	°C				

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE P	VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I <sub>DRM</sub> /I <sub>RRM</sub> MAXIMUM AT T <sub>J</sub> = T <sub>J</sub> MAXIMUM mA					
	04	400	500						
	08	800	900						
VS-ST330CL	12	1200	1300	50					
	14	1400	1500						
	16	1600	1700						

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## **VS-ST330CL Series**



## Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS		
Maximum average on-state current	1	180° condu	ction, half sine	wave	650 (314)	А		
at heatsink temperature	I <sub>T(AV)</sub>	double side	(single side) co	oled	55 (75)	°C		
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink temp	erature double side cooled	1230			
		t = 10 ms	No voltage		9000			
Maximum peak, one-cycle non-repetitive surge current		t = 8.3 ms	reapplied		9420	A		
	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		7570			
		t = 8.3 ms	reapplied	Sinusoidal half wave,	7920			
	l <sup>2</sup> t	t = 10 ms	No voltage reapplied	initial $T_J = T_J$ maximum	405	- kA <sup>2</sup> s		
Maximum 12t fay fusing		t = 8.3 ms			370			
Maximum I <sup>2</sup> t for fusing		t = 10 ms	100 % V <sub>RRM</sub>		287			
		t = 8.3 ms	reapplied		262			
Maximum I <sup>2</sup> $\sqrt{t}$ for fusing	l²√t	t = 0.1 to 10	) ms, no voltage	reapplied	4050	kA²√s		
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	$x  _{T(AV)} < l < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.91	v		
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	), T <sub>J</sub> = T <sub>J</sub> maxin	num	0.93	v		
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x π	$x  _{T(AV)} < l < \pi x$	$I_{T(AV)}$ ), $T_J = T_J$ maximum	0.57	mΩ		
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi x I_{T(AV)}), T_J = T_J maximum$			0.57	1115.2		
Maximum on-state voltage	V <sub>TM</sub>	I <sub>pk</sub> = 1730 A	$A, T_J = T_J maxim$	um, t <sub>p</sub> = 10 ms sine pulse	1.90	V		
Maximum holding current	Ι <sub>Η</sub>	T _ 05 °C	anada ayarki 1	2. V registive lead	600	mA		
Typical latching current	١L	1J=25 C,	anoue supply 1	2 V resistive load	1000			

SWITCHING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,t_r \leq 1~\mu s$ $T_J$ = $T_J$ maximum, anode voltage $\leq 80~\%~V_{DRM}$	1000	A/µs					
Typical delay time	t <sub>d</sub>	Gate current 1 A, dl <sub>g</sub> /dt = 1 A/ $\mu$ s V <sub>d</sub> = 0.67 % V <sub>DRM</sub> , T <sub>J</sub> = 25 °C	1.0						
Typical turn-off time	tq	$I_{TM}$ = 550 A, $T_J$ = $T_J$ maximum, dl/dt = 40 A/µs, $V_R$ = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ $t_p$ = 500 µs	100	μs					

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/µs				
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	50	mA				



TRIGGERING							
PARAMETER	SYMBOL	тес	VAL	UNITS			
FANAIWETEN	RAMETER SYMBOL TEST CONDITIONS		Тур.	Max.	UNITS		
Maximum peak gate power	$P_{GM}$	$T_J = T_J$ maximum,	t <sub>p</sub> ≤ 5 ms	10	0.0	w	
Maximum average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	vv	
Maximum peak positive gate current	I <sub>GM</sub>	$T_J = T_J$ maximum,	t <sub>p</sub> ≤ 5 ms	3	.0	А	
Maximum peak positive gate voltage	$+V_{GM}$		t < 5 mg	20		v	
Maximum peak negative gate voltage	-V <sub>GM</sub>	ij = ij maximum,	$T_J = T_J$ maximum, $t_p \le 5$ ms			v	
		$T_J = -40 \ ^\circ C$		200	-		
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C		100	200	mA	
		T <sub>J</sub> = 125 °C	Maximum required gate trigger/ current/voltage are the lowest	50	-		
		T <sub>J</sub> = -40 °C	value which will trigger all units 12 V anode to cathode applied	2.5	-		
DC gate voltage required to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C	12 v anoue to cathoue applied	1.8	3.0	V	
		T <sub>J</sub> = 125 °C		1.1	-		
DC gate current not to trigger	I <sub>GD</sub>	T T movimum	Maximum gate current/voltage not to trigger is the maximum		0	mA	
DC gate voltage not to trigger	$V_{GD}$	$T_J = T_J maximum$	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.25		V	

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum operating junction temperature range	TJ		-40 to +125	o°.			
Maximum storage temperature range	T <sub>Stg</sub>		-40 to +150	C			
Maximum thermal resistance, junction to heatsink	Р	DC operation single side cooled	0.11				
Maximum thermal resistance, junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.06	K/W			
Maximum thermal resistance, case to heatsink	D	DC operation single side cooled	0.011	r\/ vv			
Maximum thermal resistance, case to heatsink	$R_{thC-hs}$	DC operation double side cooled	0.005				
Mounting force, ± 10 %			9800 (1000)	N (kg)			
Approximate weight			250	g			
Case style		See dimensions - link at the end of datasheet	TO-200AC (	B-PUK)			

CONDUCTION ANGLE	SINUSOIDAL	CONDUCTION	RECTANGULA	R CONDUCTION	TEAT CONDITIONS	UNITS		
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE TEST CONDITIONS		UNITS		
180°	0.012	0.010	0.008	0.008				
120°	0.014	0.015	0.014	0.014				
90°	0.018	0.018	0.019	0.019	$T_J = T_J$ maximum	K/W		
60°	0.026	0.027	0.027	0.028				
30°	0.045	0.046	0.046	0.046				

Note

• The table above shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC

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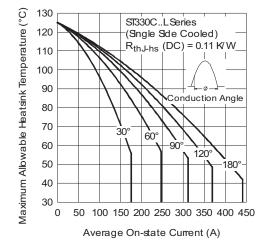


Fig. 1 - Current Ratings Characteristics

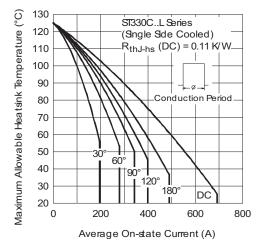


Fig. 2 - Current Ratings Characteristics

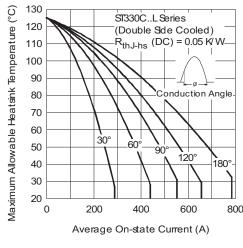


Fig. 3 - Current Ratings Characteristics

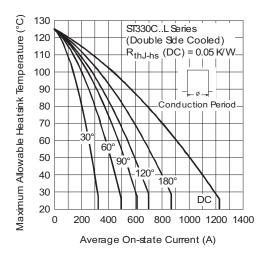


Fig. 4 - Current Ratings Characteristics

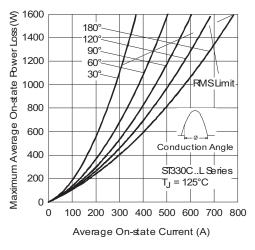
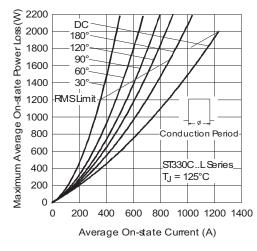
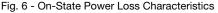


Fig. 5 - On-State Power Loss Characteristics

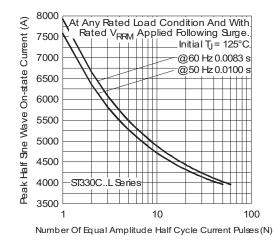




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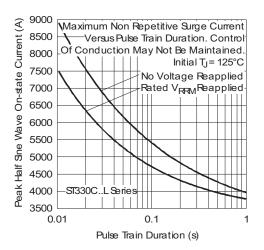
4

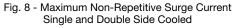
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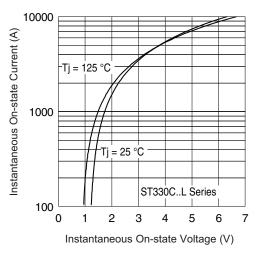


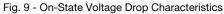
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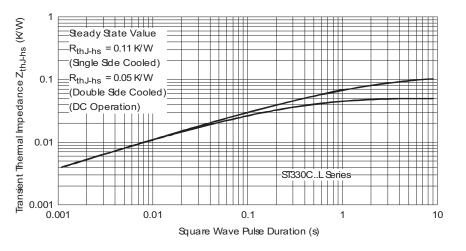


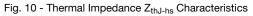




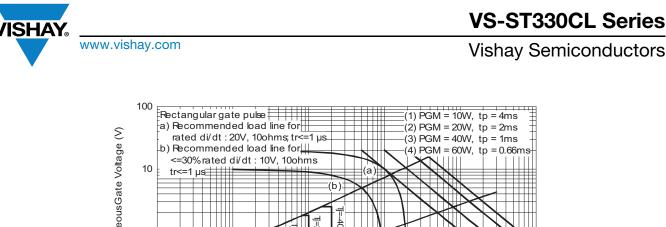


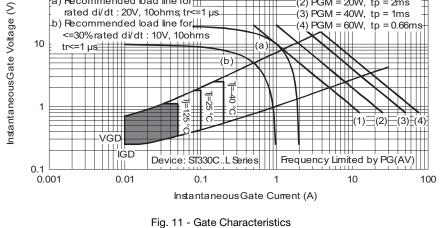






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#### **ORDERING INFORMATION TABLE**

Device code	VS-	ST	33	0	С	16	L	1	-	
	1	2	3	4	5	6	7	8	9	
	1 -   2 -   3 -   4 -   5 -   6 -   7 -   8 -	Thy Ess 0 = C = Volt L = 0 = 1 =	ristor ential p convert ceramic age coo PUK ca eyelet to fast-on	de x 100 se TO-2 erminals terminal	per = V <sub>RRN</sub> 200AC ( s (gate a s (gate	₁ (see V B-PUK) and auxi and aux	iliary ca kiliary ca	thode u	table) nsolderec unsoldere	ed leads)
	9 -	3 =	fast-on	terminal dt: ● No	s (gate	and aux 0 V/µs (	kiliary ca (standai	athode s rd selec	soldered I tion)	

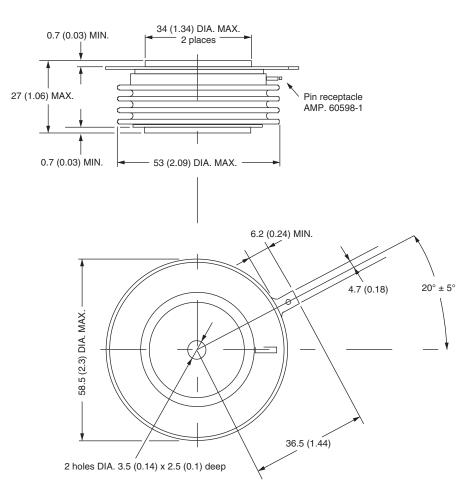
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95076				



## TO-200AC (B-PUK)

#### **DIMENSIONS** in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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